

**DL-3038-033****Index Guided AlGaInP Laser Diode****Overview**

DL-3038-033 is index guided 635 nm (Typ.) AlGaInP laser diode with low threshold current and high operating temperature.

Low threshold current and short wavelength are achieved by a strained multiple quantum well active layer. The lasing wavelength is 635 nm which is 8 times brighter than that of 670 nm lasers. DL-3038-033 is suitable for applications such as bar-code scanners, laser pointers and other optical information systems.

Features

- Short wavelength : 635 nm (Typ.)
- Low threshold current : $I_{th} = 30$ mA (Typ.)
- High operating temperature : 50°C at 5 mW
- Low operating voltage : $V_{op} = 2.2$ V (Typ.)

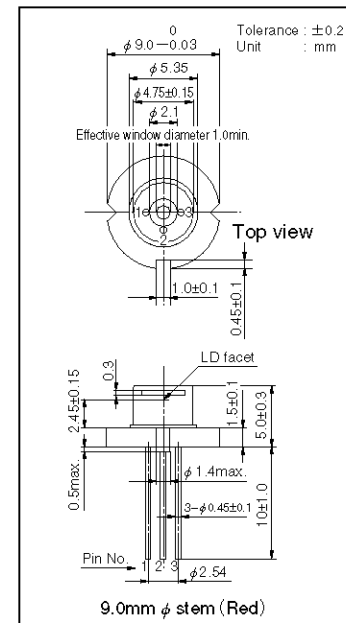
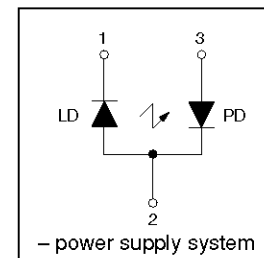
Absolute Maximum Ratings at $T_c=25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit	
Light Output	P_o	5	mW	
Reverse Voltage	Laser PIN	V_R	2	V
			30	
Operating Temperature	T_{opr}	-10 to +50	°C	
Storage Temperature	T_{stg}	-40 to +85	°C	

Electrical and Optical Characteristics at $T_c=25^\circ\text{C}$

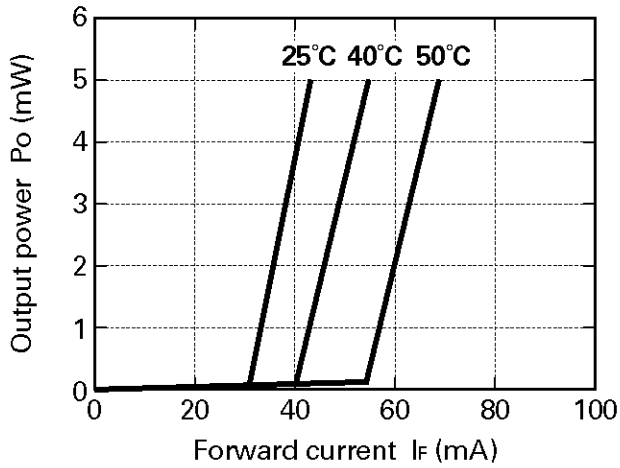
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current	I_{th}	CW	—	30	50	mA
Operating Current	I_{op}	$P_o=5\text{mW}$	—	40	60	mA
Operating Voltage	V_{op}	$P_o=5\text{mW}$	—	2.2	2.4	V
Lasing Wavelength	λ_p	$P_o=5\text{mW}$	—	635	640	nm
Beam Divergence ※)	Perpendicular	θ_{\perp}	25	35	40	deg.
	Parallel	θ_{\parallel}	6	8	10	deg.
Off Axis Angle	Perpendicular	$\Delta\theta_{\perp}$	—	—	±3	deg.
	Parallel	$\Delta\theta_{\parallel}$	—	—	±3	deg.
Differential Efficiency	dP_o/dI_{op}	—	—	0.4	—	mW/mA
Monitoring Output Current	I_m	$P_o=5\text{mW}$	0.10	0.20	0.50	mA
Astigmatism	A_s	$P_o=5\text{mW}$	—	8	—	μm

※) Full angle at half maximum note : The above product specifications are subject to change without notice.

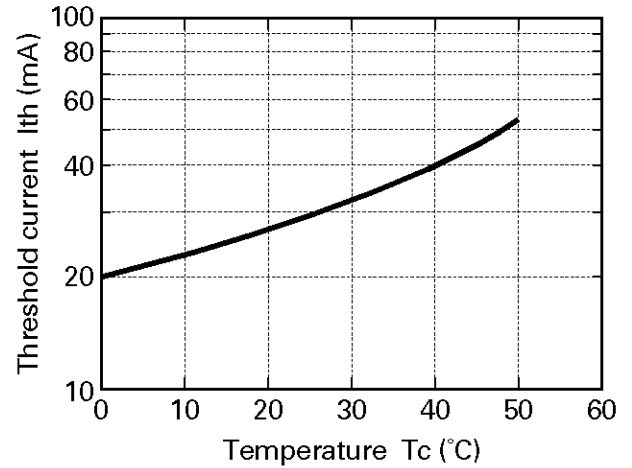
Package Dimensions**Electrical Connection**

Characteristics

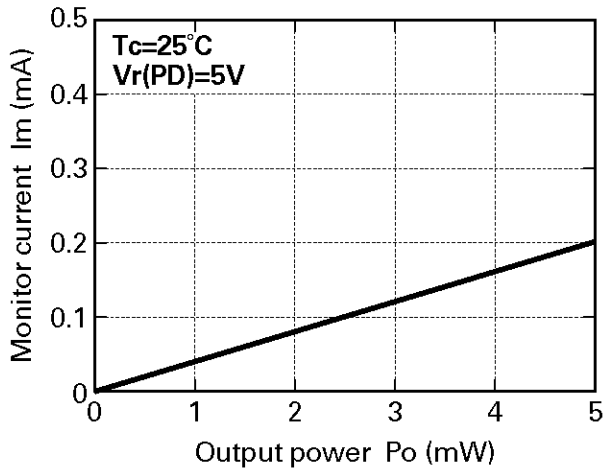
Output power vs. Forward current



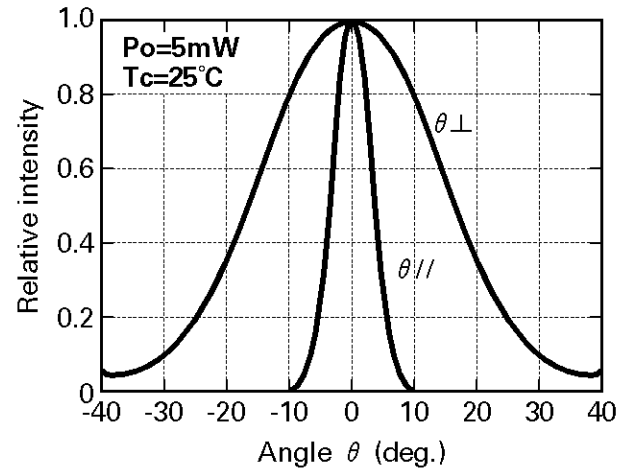
Threshold current vs. Temperature



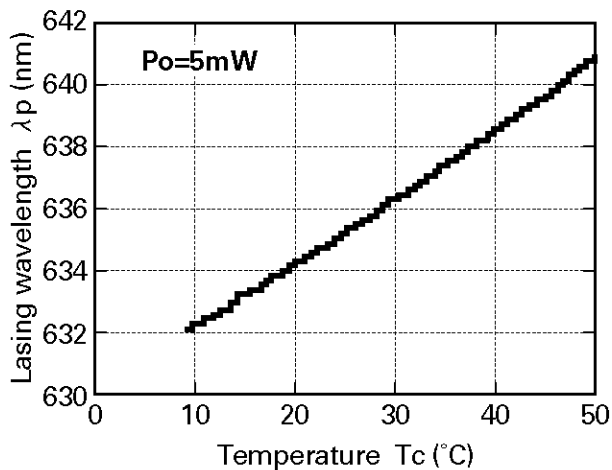
Monitor current vs. Output power



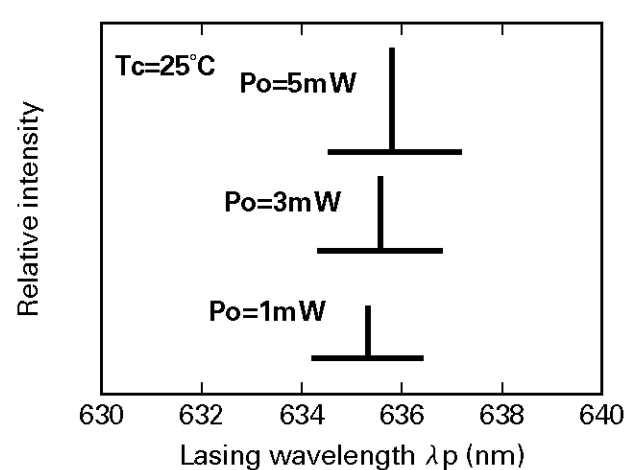
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



CAUTION

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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

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